

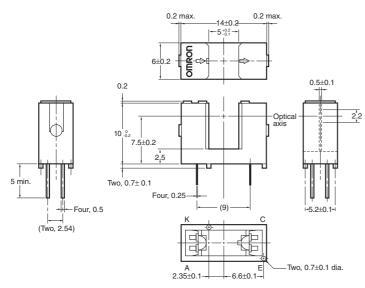
Photomicrosensor (Transmissive) **FF-SX1041**



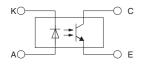
Be sure to read Precautions on page 25.

Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Terminal No.	Name	
Α	Anode	
K	Cathode	
С	Collector	
E	Emitter	

Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.3
3 < mm ≤ 6	±0.375
6 < mm ≤ 10	±0.45
10 < mm ≤ 18	±0.55
18 < mm ≤ 30	±0.65

■ Features

- General-purpose model with a 5-mm-wide slot.
- PCB mounting type.
- High resolution with a 0.5-mm-wide aperture.

■ Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Rated value
Emitter	Forward current	I _F	50 mA (see note 1)
	Pulse forward cur- rent	I _{FP}	1 A (see note 2)
	Reverse voltage	V_R	4 V
Detector	Collector–Emitter voltage	V _{CEO}	30 V
	Emitter–Collector voltage	V _{ECO}	
	Collector current	I _C	20 mA
	Collector dissipa- tion	P _c	100 mW (see note 1)
Ambient tem-	Operating	Topr	–25°C to 95°C
perature	Storage	Tstg	–30°C to 100°C
Soldering temp	erature	Tsol	260°C (see note 3)

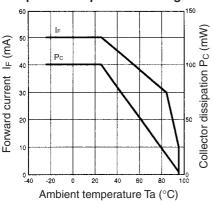
- **Note: 1.** Refer to the temperature rating chart if the ambient temperature exceeds 25°C.
 - 2. The pulse width is 10 μs maximum with a frequency of 100 Hz.
 - 3. Complete soldering within 10 seconds.

■ Electrical and Optical Characteristics (Ta = 25°C)

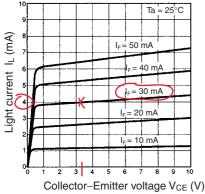
	Item	Symbol	Value	Condition
Emitter	Forward voltage	V_{F}	1.2 V typ., 1.5 V max.	I _F = 30 mA
	Reverse current	I _R	0.01 μA typ., 10 μA max.	V _R = 4 V
	Peak emission wavelength	λ_{P}	940 nm typ.	I _F = 20 mA
Detector	Light current	Ι _L	0.5 mA min., 14 mA max.	$I_F = 20 \text{ mA}, V_{CE} = 10 \text{ V}$
	Dark current	I _D	2 nA typ., 200 nA max.	V _{CE} = 10 V, 0 ℓx
	Leakage current	I _{LEAK}		
	Collector–Emitter saturated voltage	V _{CE} (sat)	0.1 V typ., 0.4 V max.	$I_F = 20 \text{ mA}, I_L = 0.1 \text{ mA}$
	Peak spectral sensitivity wave- length	λ_{P}	850 nm typ.	V _{CE} = 10 V
Rising time		tr	4 μs typ.	$V_{CC} = 5 \text{ V}, R_{L} = 100 \Omega, I_{L} = 5 \text{ mA}$
Falling time)	tf	4 μs typ.	$V_{CC} = 5 \text{ V}, R_L = 100 \Omega, I_L = 5 \text{ mA}$

■ Engineering Data

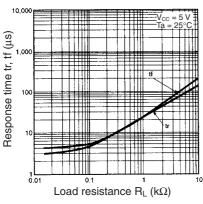
Forward Current vs. Collector Dissipation Temperature Rating



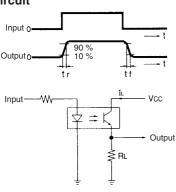
Light Current vs. Collector–Emitter Voltage Characteristics (Typical)



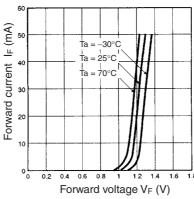
Response Time vs. Load Resistance Characteristics (Typical)



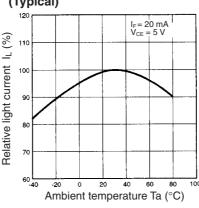
Response Time Measurement Circuit



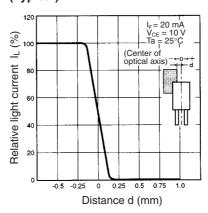
Forward Current vs. Forward Voltage Characteristics (Typical)



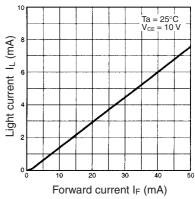
Relative Light Current vs. Ambient Temperature Characteristics (Typical)



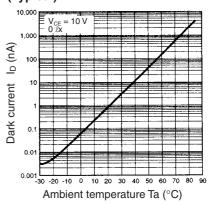
Sensing Position Characteristics (Typical)



Light Current vs. Forward Current Characteristics (Typical)



Dark Current vs. Ambient Temperature Characteristics (Typical)



Sensing Position Characteristics (Typical)

